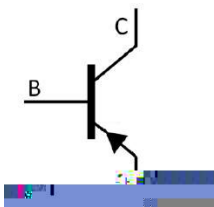
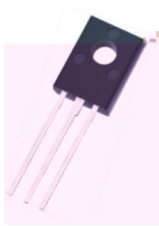


WR04591 M M E S Q S A M y s I I 1 Silicon PNP transistor in a TO-126F Plastic Package.

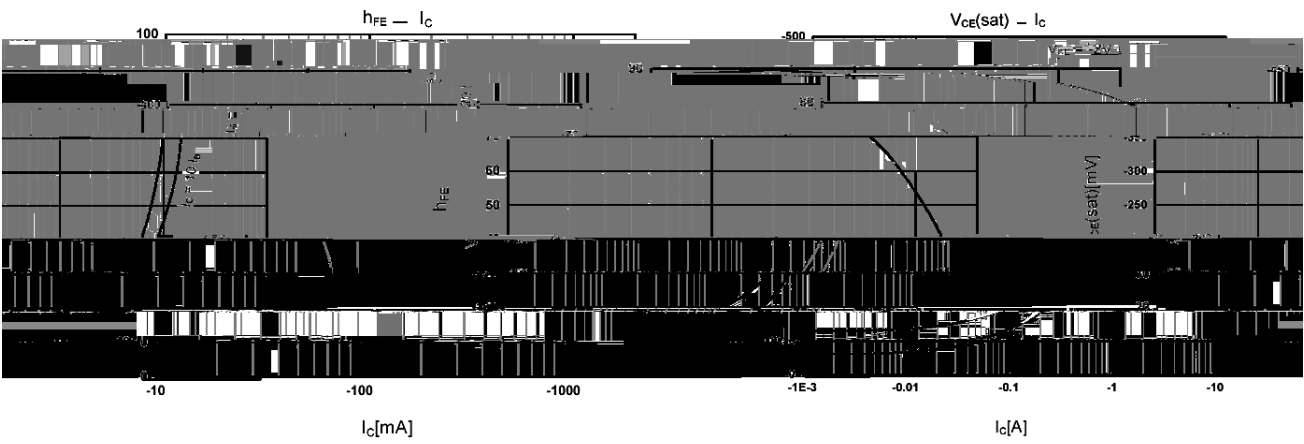
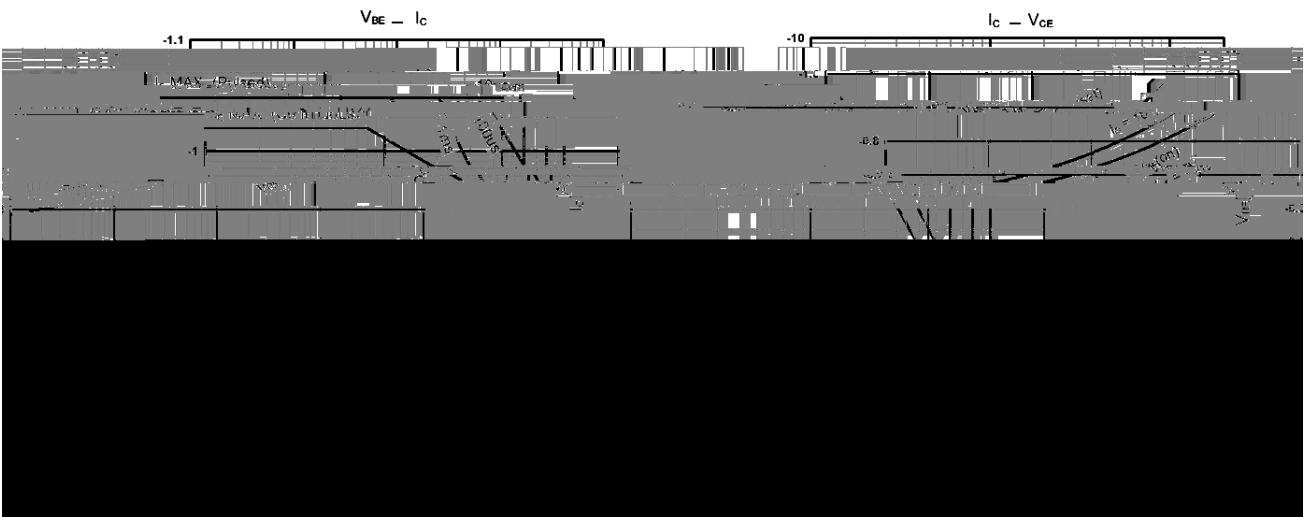
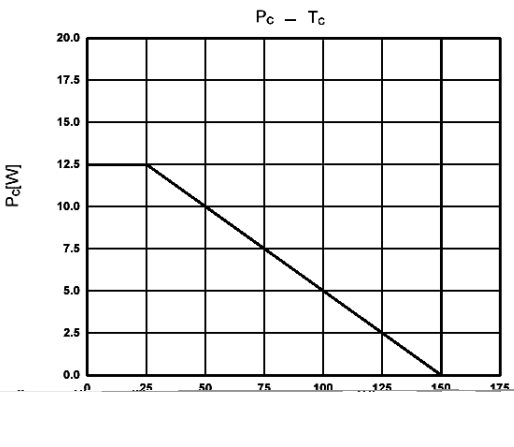
ль EG46: Й, '
 Complement to BD137.

Medium power linear and switching applications.

PIN1 χ EmitterPIN 2 χ CollectorPIN 3 χ Base

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V

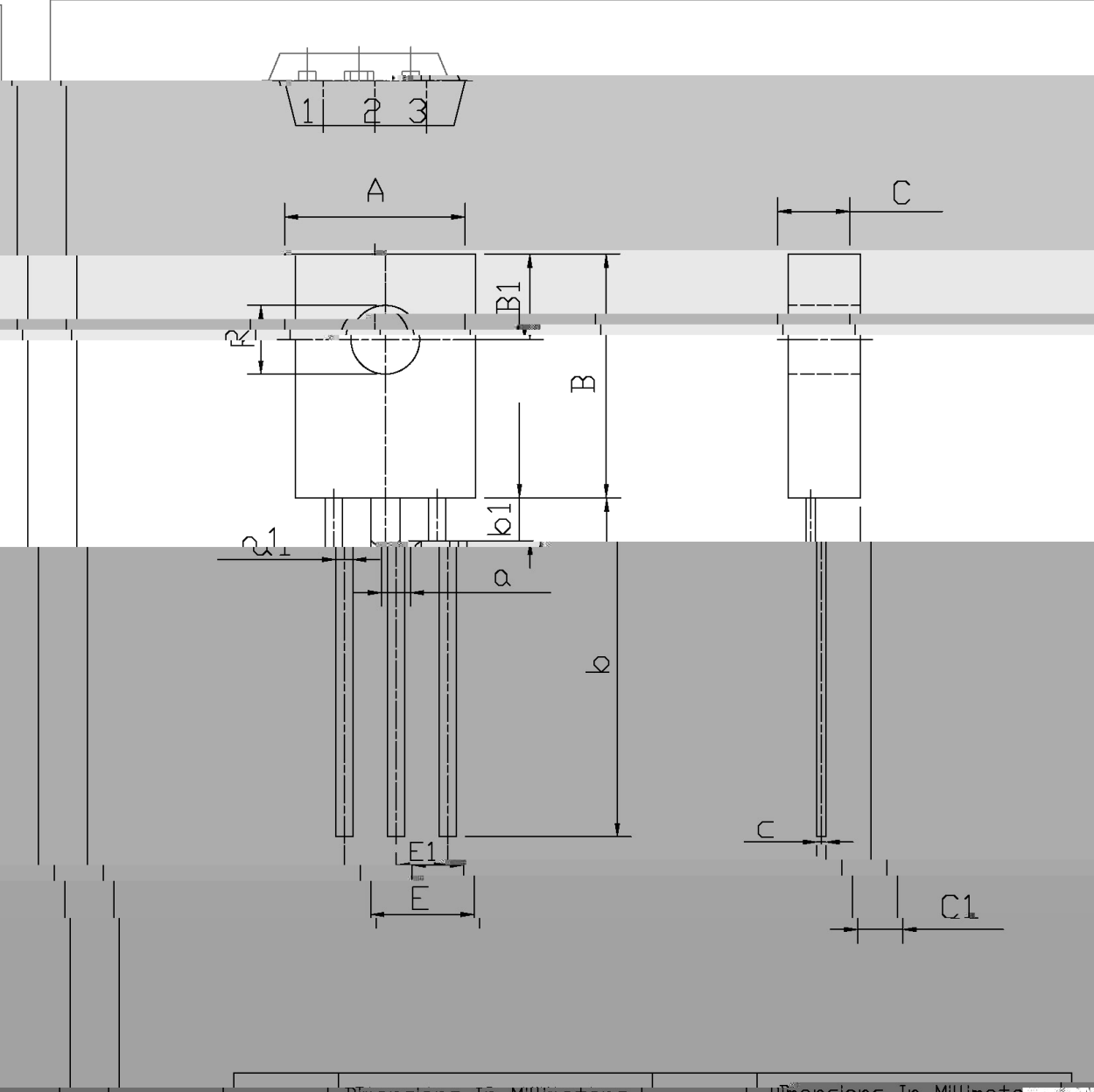
/ Electrical Characteristic Curve



/ Package Dimensions

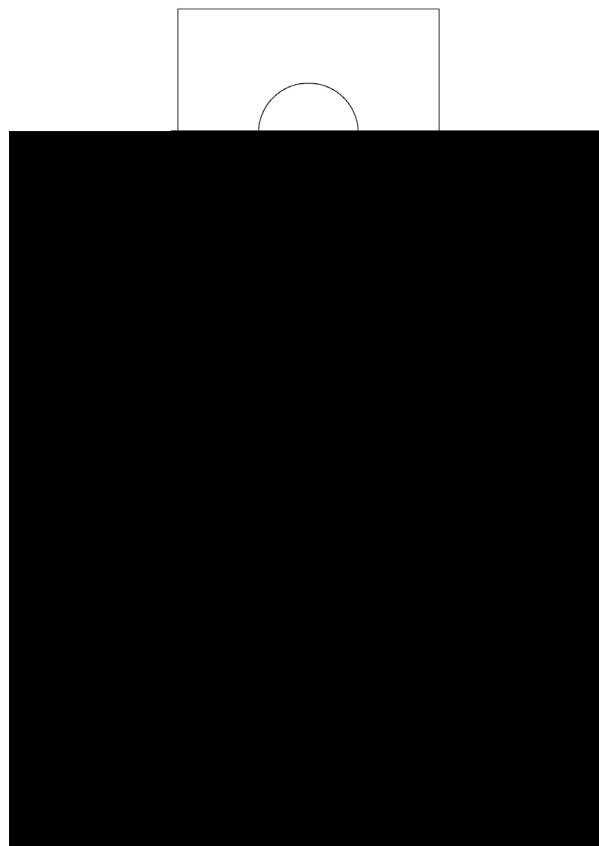
TU-126F

单位: mm



Symbol	Min	Max	Symbol	Min	Max
A	7.8	8.2	a1	0.65	0.8
B	10.9	11.0	E	1.4	1.5

/ Marking Instructions



Б " X

EU X

EG46; X

49:

---- X

Note:

BR:

BD138:

16:

****:

Б 3 " П

Б F β 3 N

Б k_{1H} ' 6 П

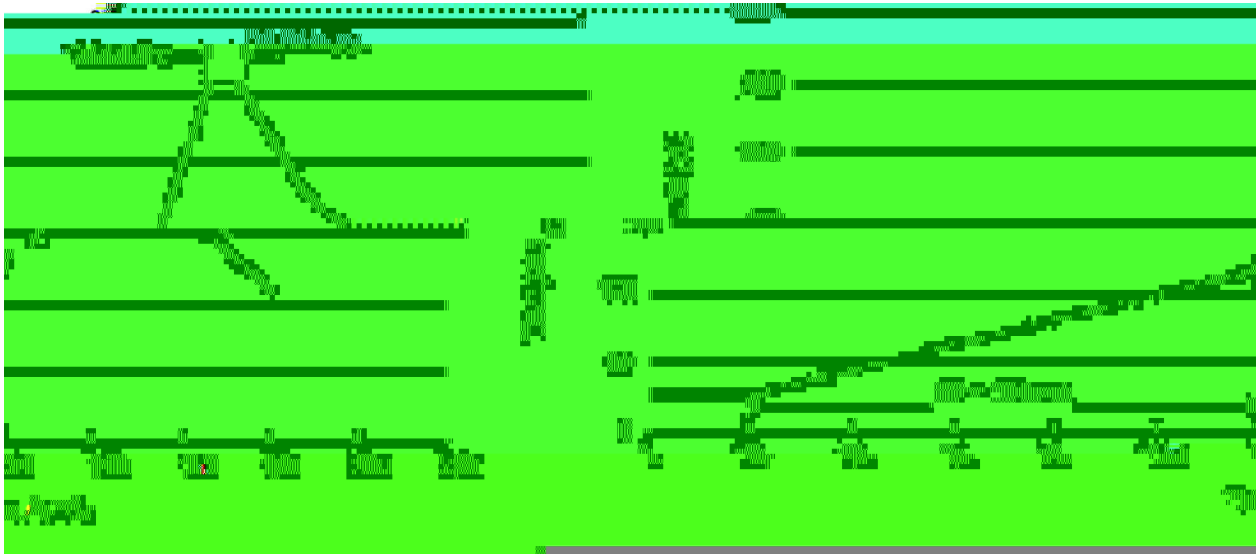
Б 1 F 1 N П 1 6 1 F 1 N П

Company Code

Product Type.

h_{FE} Classifications Symbol

Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)


б " X

1. 150°C ~ 255°C, Time: 60~90sec;

2. 255°C, Duration: 5~10sec;

3. Cooling Speed: 2~10°C/sec.

Note:

1.Preheating:25~150 °C , Time:60~90sec.

2.Peak Temp.:255 °C , Duration:5 ~ 10sec.

3. Cooling Speed: 2~10 °C /sec.

/ Resistance to Soldering Heat Test Conditions

1. 270°C ± 5°C

2. 10 ± 1 sec.

Temp.:270±5

Time:10±1 sec

/ Packaging SPEC.

1. BULK

Package Type	Units		Dimension		(unit mm ³)
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Boxes	
	1	1	1	1	